



Low Voltage, Dual DPDT and Quad SPDT Analog Switches

DESCRIPTION

The DG2018 and DG2019 are low voltage, single supply analog switches. The DG2018 is a dual double-pole/double-throw (DPDT) with two control inputs that each controls a pair of single-pole/double-throw (SPDT). The DG2019 uses one control pin to operate four independent SPDT switches.

When operated on a + 3 V supply, the DG2018's control pins are compatible with 1.8 V digital logic. The DG2019 has an available feature of a V_L pin that allows a 1.0 V threshold for the control pin when V_L is powered with 1.5 V.

Built on Vishay Siliconix's low voltage submicron CMOS process, the DG2018 and DG2019 are ideal for high performance switching of analog signals; providing low onresistance (6 Ω at + 2.7 V), fast speed (Ton, Toff at 42 ns and 16 ns), and a bandwidth that exceeds 180 MHz.

The DG2018 and DG2019 were designed to offer solutions that extend beyond audio/video functions, to providing the performance required for today's demanding mixed-signal switching in portable applications.

An epitaxial layer prevents latch-up. Brake-before-make is guaranteed for all SPDT's. All switches conduct equally well in both directions when on, and blocks up to the power supply level when off.

DG2018DN

FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- · Low on resistance
 - R_{DS(on)}: 6 Ω at 2.7 V
- · Low voltage logic compatible
 - DG2019: V_{INH} = 1 V
- · High bandwidth: 180 MHz
- QFN-16 package

BENEFITS

- · Ideal for both analog and digital signal switching
- Reduced power consumption
- High accuracy
- · Reduced PCB space
- · Fast switching
- Low leakage

APPLICATIONS

- · Cellular phones
- · Audio and video signal routing
- PCMCIA cards
- · Battery operated systems
- · Portable instrumentation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

QFN-16 (3 X 3) V+ COM1 NO1 NC4 15 14 13 16 NC₁ COM4 NO4 IN1, IN2 NO₂ IN3, IN4 COM₂ NC3 NO3 COM3 GND Top View

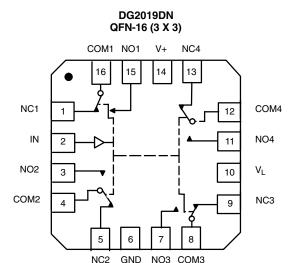
TRUTH TABLE									
IN1, IN2									
Logic	NC1 and NC2	NO1 and NO2							
0	ON	OFF							
1	OFF	ON							
IN3, IN4									
Logic	NC3 and NC4	NO3 and NO4							
0	ON	OFF							
1	OFF	ON							

ORDERING INFORMATION									
Temp. Range Package Part Number									
- 40 °C to 85 °C	QFN-16 (3 x 3 mm)	DG2018DN							

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FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Top View

TRUTH TABLE									
Logic	NC1, 2, 3 and 4	NO1, 2, 3 and 4							
0	ON	OFF							
1	OFF	ON							

ORDERING INFORMATION									
Temp. Range Package Part Number									
- 40 °C to 85 °C	QFN-16 (3 x 3 mm)	DG2019DN							

ABSOLUTE MAXIMUM RATINGS									
Parameter	Limit	Unit							
Reference V+ to GND	- 0.3 to + 6	V							
IN, COM, NC, NO	- 0.3 to (V+ + 0.3)	7 V							
Continuous Current (Any terminal)	± 50	mΛ							
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)	± 100	- mA							
Storage Temperature (D Suffix)	- 65 to 150	°C							
Power Dissipation (Packages) ^b	QFN-16 (3 x 3 mm) ^c	850	mW						

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.
- c. Derate 4.0 mW/°C above 70 °C.





SPECIFICATIONS V+	- U	Test Conditions				Limits		
		Otherwise Unless Specific	ed		- 40 °C to 85 °C			
		$V+ = 3 V, \pm 10 \%,$	0					
		(DG2018 Only) $V_{IN} = 0.5 \text{ or } 1.6 \text{ m}$			_			
Parameter	Symbol	(DG2019 Only) V _L = 1.5 V, V _{IN} = 0.4	4 or 1.0 V°	Temp. ^a	Min.b	Typ. ^c	Max. ^b	Unit
Analog Switch	\/ \/			ı		Π	Π	
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}			Full	0		V+	V
On-Resistance	R _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 0.2 \text{ V}/1.9$ $I_{NO}, I_{NC} = 10 \text{ mA}$	5 V	Room Full		6	12 15	
R _{ON} Flatness	R _{ON} Flatness	V+ = 2.7 V	Room		0.5	2	Ω	
R _{ON} Match Between Channels	ΔR _{ON}	$V_{COM} = 0$ to V+, I_{NO} , $I_{NC} = 10$	$V_{COM} = 0$ to V+, I_{NO} , $I_{NC} = 10$ mA			0.6	3	
Switch Off Leakage Current	$I_{NO(off)} = I_{NC(off)} V_{+} = 3.3 \text{ V}, V_{NO}, V_{NC} = 0.3 \text{ V/3 V}$		Room Full	- 1 - 10	0.3	1 10		
emion on Lounage euroni	I _{COM(off)}	$V_{COM} = 3 \text{ V}/0.3 \text{ V}$	Room Full	- 1 - 10	0.3	1 10	nA	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 3.3 V, V_{NO}, V_{NC} = V_{COM} = 0$	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V/3 V}$				1 10	
Digital Control			i .	1		•	•	
Input High Voltage	V _{INH}		DG2018	Full	1.4			
		V _L = 1.5 V	DG2019	Full	1.0			V
Input Low Voltage	V_{INL}	V _L = 1.5 V	DG2018 DG2019	Full Full			0.5	
Input Capacitance	C _{in}	f = 1 MHz	DG2019	Full		9	0.4	pF
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ or } V+$		Full	- 1	9	1	μΑ
Dynamic Characteristics	·INL S. ·INH	7 IIV		ı uıı	•		<u>'</u>	μ
-				Room		42	55	
Turn-On Time	t _{ON}	V_{NO} or $V_{NC} = 2.0 \text{ V}$, $R_{I} = 300 \Omega$, C	ı = 35 pF	Full			65	
Turn-Off Time	t _{OFF}			Room Full		16	25 35	ns
Break-Before-Make Time	t _d	V_{NO} or V_{NC} = 2.0 V, R_L = 50 Ω , C_L	_ = 35 pF	Full	1			
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} =$	= 0 Ω	Room		- 1.46		рC
Off-Isolation ^d	OIRR			Room		- 67		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 M$	1Hz	Room		- 72		ub
Bandwidth ^d	BW		Room		180		MHz	
N. N. 0" 0 't d	C _{NO(off)}			Room		9		
N _O , N _C Off Capacitance ^d	C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		9		- pF	
Observation d	C _{NO(on)}	$v_{IN} = 0$ or v_{+} , $i = 1$ with z_{-}	Room		30			
Channel-On Capacitance ^d C _{NC(on}			Room		30			
Power Supply								
Power Supply Current	l+	$V_{IN} = 0$ or $V+$		Full		0.01	1.0	μΑ

Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
 c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.

DG2018, DG2019

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SPECIFICATIONS V+ =	= 5 V							
		Test Conditions Otherwise Unless Specifion V+ = 5 V, ± 10 %,		- 40	Limits 0 °C to 85	5°C		
		(DG2018 Only) V _{IN} = 0.8 or 1	.8 V ^e					
Parameter	Symbol	(DG2019 Only) V _L = 1.5 V, V _{IN} = 0	.4 or 1.0 V ^e	Temp.a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch	ľ					I	l	ı
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V	
On-Resistance	R _{ON}	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC}$	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$				8 10	
R _{ON} Flatness	R _{ON} Flatness	$V_{+} = 4.5 V$ $V_{COM} = 0 \text{ to } V_{+}, I_{NO}, I_{NC} = 10$	Room		0.6	1.2	Ω	
R _{ON} Match Between Channels	ΔR_{ON}	VCOM = 0 to V+, INO, INC = 10	UIIIA	Room		0.6	1.2	
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V			- 1 - 10	0.03	1 10	
Switch On Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V/4.5 V}$, $V_{COM} = 4$.5 V/1 V	Room Full	- 1 - 10	0.03	1 10	nA
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 5.5 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 10$	1 V/4.5 V	Room Full	- 1 - 10	0.03	1 10	
Digital Control				1		•	•	ı
Input High Voltage	V _{INH}	V _I = 1.5 V	DG2018	Full	1.8			
		V _L = 1.5 V	DG2019	Full Full	1.0		0.0	٧
Input Low Voltage	V _{INL}	V _L = 1.5 V	DG2018 DG2019	Full			0.8	
Input Capacitance	C _{in}	<u> </u>	2 0.20.0	Full		9	•••	pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+		Full	1		1	μΑ
Dynamic Characteristics		l		I		l		
Turn-On Time	t _{ON}	V_{NO} or $V_{NC} = 3$ V, $R_L = 300 \Omega$, C	= 35 nF	Room Full		44	48 52	
Turn-Off Time	t _{OFF}			Room Full		19	33 35	ns
Break-Before-Make Time	t _d	V_{NO} or $V_{NC} = 3 \text{ V}$, $R_L = 50 \Omega$, C_L		Full	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN}$	= 0 Ω	Room		- 2.46		рC
Off-Isolation ^d	OIRR			Room		- 67		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF, f = 1 N$	ИHz	Room		- 72		ub.
Bandwidth ^d	BW			Room		180		MHz
Source-Off Capacitanced	C _{NO(off)}			Room		7.5		
Source On Supacitation	C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz		Room		7.5		pF
Channel-On Capacitance ^d	C _{NO(on)}	IIV ,	Room		30			
•	C _{NC(on}		Room		30			
Power Supply		T				ı		
Power Supply Range	V+	\\ \ \O \\ \\\\\\\\\\\\\\\\\\\\\\\\\\\		F	1.8	0.04	5.5	V
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+$		Full		0.01	1.0	μΑ

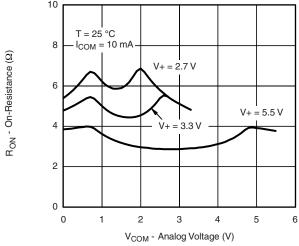
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Not production tested.

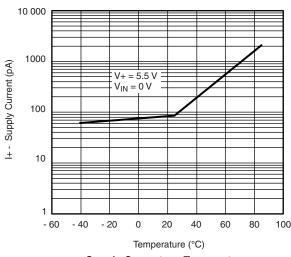
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



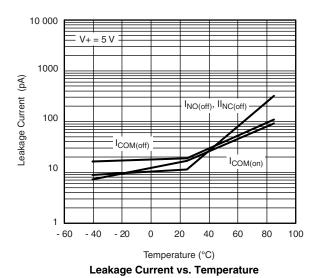
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



 R_{ON} vs. V_{COM} and Supply Voltage

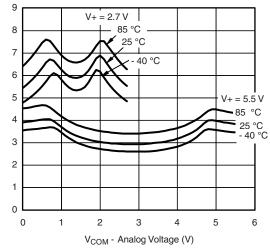


Supply Current vs. Temperature

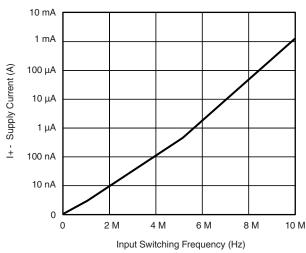


 R_ON - On-Resistance (Ω)

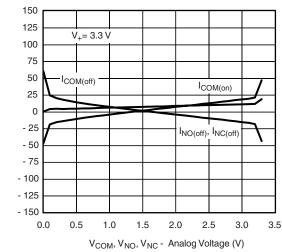
Leakage Current (pA)



R_{ON} vs. Analog Voltage and Temperature



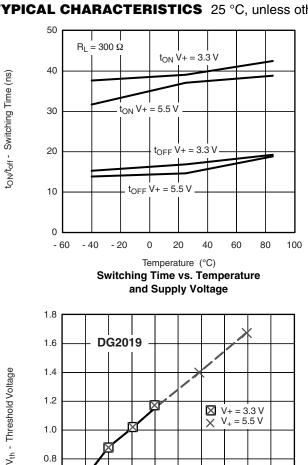
Supply Current vs. Input Switching Frequency

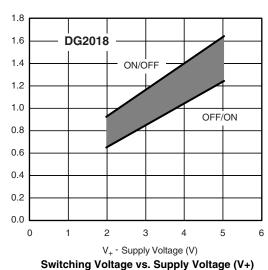


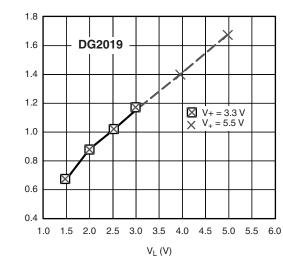
Leakage vs. Analog Voltage

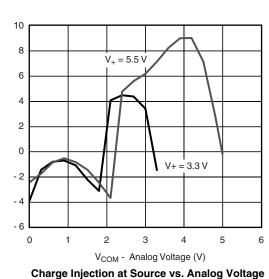
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





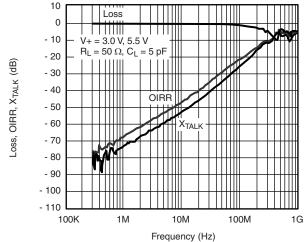






V_{th} - Threshold Voltage

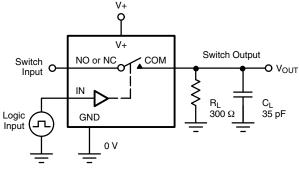
Q - Charge Injection (pC)

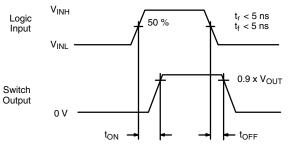


Insertion Loss, Off Isolation and Crosstalk vs. Frequency



TEST CIRCUITS





C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

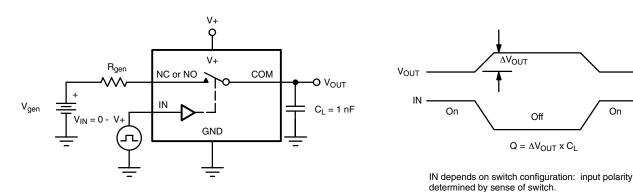


Figure 2. Charge Injection

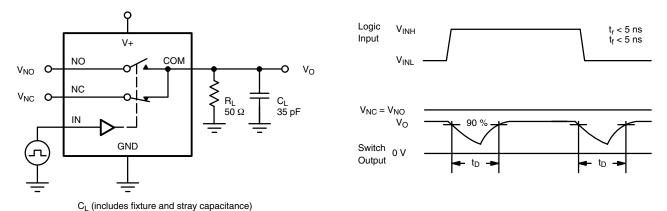


Figure 3. Break-Before-Make Interval

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TEST CIRCUITS



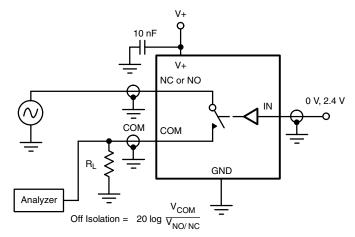


Figure 4. Off-Isolation

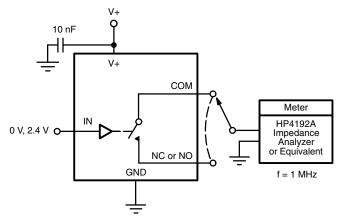
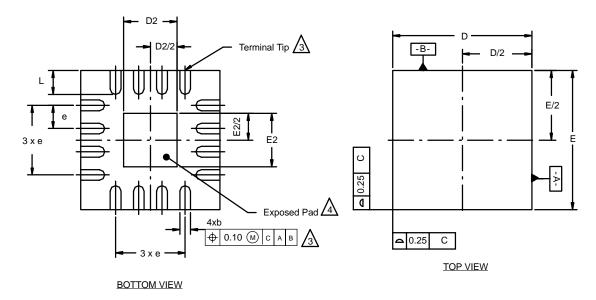


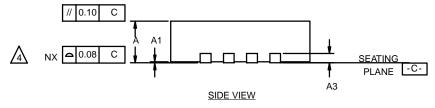
Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72342.



QFN-16 LEAD (3 X 3)





NOTES:

- 1. All dimensions are in millimeters.
- 2. N is the total number of terminals.

Dimension b applies to metallized terminal and is measured between 0.25 and 0.30 mm from terminal tip.

Coplanarity applies to the exposed heat sink slug as well as the terminal.

5. The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.

	VARIATION 1						VARIATION 2					
Dim	MILLIMETERS			ILLIMETERS INCHES		MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min Nom Max		Min	Nom	Max	
Α	0.80	0.90	1.00	0.031	0.035	0.039	0.80	0.90	1.00	0.031	0.035	0.039
b	0.18	0.23	0.30	0.007	0.009	0.012	0.18	0.25	0.30	0.007	0.010	0.012
D	3.00 BSC			0.118 BSC		3.00 BSC			0.118 BSC			
D2	1.00	1.15	1.25	0.039	0.045	0.049	1.55	1.70	1.80	0.061	0.067	0.071
Е		3.00 BSC			0.118 BSC			3.00 BSC			0.118 BSC	
E2	1.00	1.15	1.25	0.039	0.045	0.049	1.55	1.70	1.80	0.061	0.067	0.071
е	0.50 BSC				0.020 BSC			0.50 BSC			0.020 BSC	
L	0.30	0.40	0.50	0.012	0.016	0.020	0.30	0.40	0.50	0.012	0.016	0.020
ECN: S-32625—Rev. B, 29-Dec-03 DWG: 5899												

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